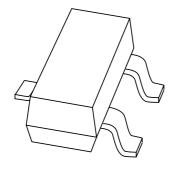
DISCRETE SEMICONDUCTORS

DATA SHEET



MMBT3904 NPN switching transistor

Product data sheet Supersedes data of 2002 Oct 04 2004 Feb 03



NPN switching transistor

MMBT3904

FEATURES

- Collector current capability I_C = 200 mA
- Collector-emitter voltage V_{CEO} = 40 V.

APPLICATIONS

• General switching and amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package. PNP complement: MMBT3906.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
MMBT3904	7A*

Note

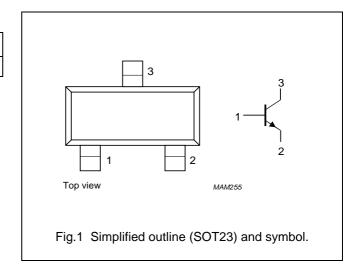
- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	40	V
I _C	collector current (DC)	200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIPE NUMBER	NAME DESCRIPTION VERSION			
MMBT3904	_	plastic surface mounted package; 3 leads SOT2		

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V_{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	200	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

^{1.} Transistor mounted on an FR4 printed-circuit board.

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

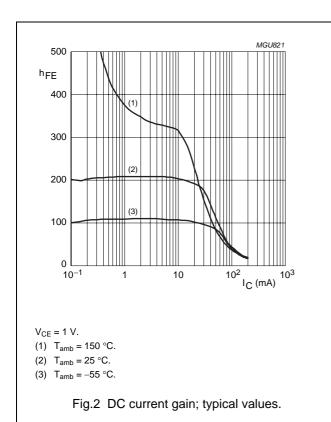
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	50	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 6 V	_	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; see Fig.2; note 1			
		$I_{\rm C} = 0.1 {\rm mA}$	60	_	
		I _C = 1 mA	80	_	
		I _C = 10 mA	100	300	
		I _C = 50 mA	60	_	
		I _C = 100 mA	30	_	
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 1 mA	_	200	mV
	voltage	I _C = 50 mA; I _B = 5 mA	_	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	650	850	mV
		I _C = 50 mA; I _B = 5 mA	_	950	mV
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 5$ V; $f = 1$ MHz	_	4	pF
C _e	emitter capacitance	$I_C = I_c = 0$; $V_{BE} = 500 \text{ mV}$; $f = 1 \text{ MHz}$	_	8	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 20 \text{ V};$ f = 100 MHz	300	_	MHz
F	noise figure	I_C = 100 μA; V_{CE} = 5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	-	5	dB
Switching ti	mes (between 10% and 90% lev	els); see Fig.3	•	•	<u> </u>
t _d	delay time	I _{Con} = 10 mA; I _{Bon} = 1 mA;	_	35	ns
t _r	rise time	I _{Boff} = -1 mA	_	35	ns
t _s	storage time		_	200	ns
t _f	fall time		_	50	ns

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

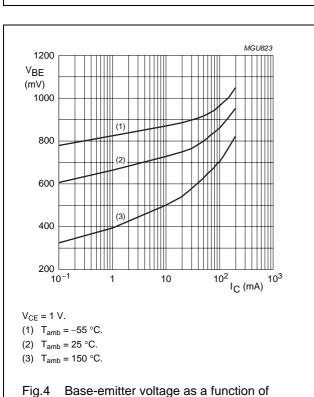
NPN switching transistor

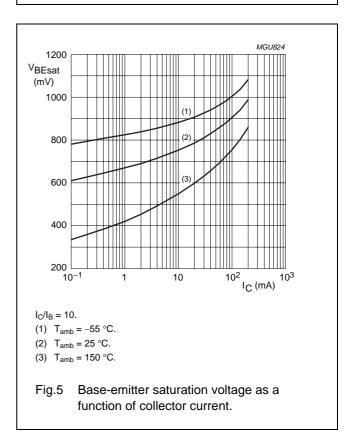
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MGU822 250 I_{C} (mA) (1) (2) (3) (4) (5) (6) 200 150 (9) 100 50 8 V_{CE} (V) 4 $T_{amb} = 25 \, ^{\circ}C.$ (1) $I_B = 5 \text{ mA}$. (5) $I_B = 3 \text{ mA}$. (9) $I_B = 1 \text{ mA}$. (10) $I_B = 0.5 \text{ mA}$. (2) $I_B = 4.5 \text{ mA}.$ (6) $I_B = 2.5 \text{ mA}.$ (7) $I_B = 2 \text{ mA}$. (3) $I_B = 4 \text{ mA}$. (4) $I_B = 3.5 \text{ mA}.$ (8) $I_B = 1.5 \text{ mA}.$ Fig.3 Collector current as a function of

collector-emitter voltage.



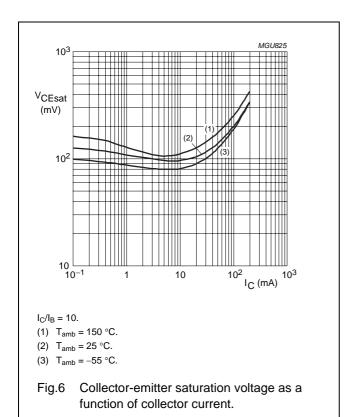


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collector current.

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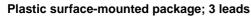


 $V_{i} = 5 \text{ V; T} = 500 \text{ µs; } t_{p} = 10 \text{ µs; } t_{r} = t_{l} \leq 3 \text{ ns.}$ $R1 = 56 \Omega; R2 = 2.5 \text{ kΩ; } R_{B} = 3.9 \text{ kΩ; } R_{C} = 270 \Omega.$ $V_{BB} = -1.9 \text{ V; V}_{CC} = 3 \text{ V.}$ Oscilloscope: input impedance $Z_{i} = 50 \Omega.$

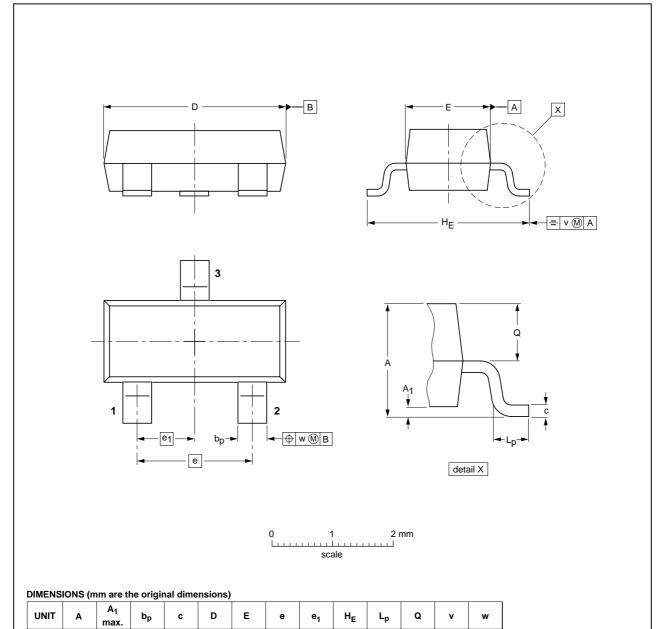
NPN switching transistor

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PACKAGE OUTLINE



SOT23



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DAT	
SOT23		TO-236AB				-04-11-04 06-03-16

1.9

0.45

0.55

0.1

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0.48

0.38

0.9

NPN switching transistor

MMBT3904

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Contact information

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